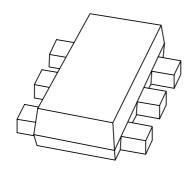
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG1020EVUltra low V_F MEGA Schottky barrier rectifier

Product specification

2003 Jul 15





Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

FEATURES

Forward current: 2 AReverse voltage: 10 VUltra low forward voltage

Ultra small plastic SMD package.

APPLICATIONS

· Low voltage rectification

• High efficiency DC/DC conversion

• Switch mode power supply

· Inverse polarity protection

• Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection encapsulated in a SOT666 ultra small plastic SMD package.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode
3	anode
4	anode
5	cathode
6	cathode

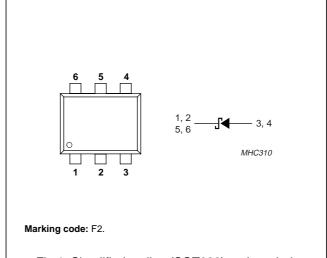


Fig.1 Simplified outline (SOT666) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	10	V
I _F	continuous forward current T _{sp} ≤ 55 °C; note 1		_	2	Α
I _{FRM}	repetitive peak forward current	$t_p \le 1$ ms; $\delta \le 0.5$; note 1	_	3.2	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms square wave; note 1	_	9	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Only valid if pins 3 and 4 are connected in parallel.

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ELECTRICAL CHARACTERISTICS

 $T_{amb} = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	forward voltage	see Fig.2; note 1			
		I _F = 0.01 A	100	130	mV
		I _F = 0.1 A	164	200	mV
		I _F = 1 A	255	350	mV
		I _F = 2 A	306	460	mV
I _R	reverse current	see Fig.3 note 2			
		V _R = 5 V	0.7	2	mA
		V _R = 8 V	1	2.5	mA
		V _R = 10 V	1.2	3	mA
C _d	diode capacitance	$V_R = 5 \text{ V}$; f = 1 MHz; see Fig.4	37	45	pF

Notes

- 1. Pulse test: $t_p = 300 \,\mu s$; $\delta = 0.02$.
- 2. For Schottky barrier rectifiers thermal runaway has to be considered, as in some applications the reverse power losses (P_R) are a significant part of the total power losses.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	405	K/W
		note 2	215	K/W
R _{th j-s}	thermal resistance from junction to solder point	note 3	80	K/W

Notes

- 1. Refer to SOT666 standard mounting conditions.
- 2. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for cathode 1 cm².
- 3. Solder point of cathode tabs.

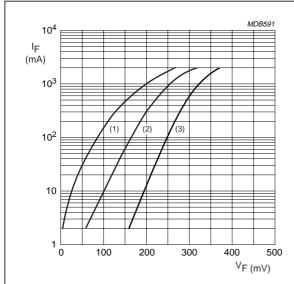
Soldering

Reflow soldering is the only recommended soldering method.

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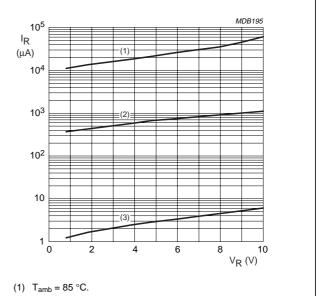
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GRAPHICAL DATA



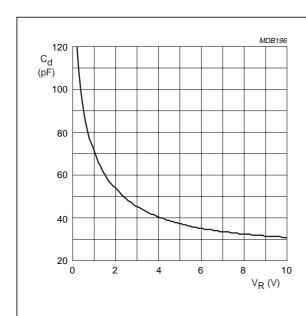
- (1) $T_{amb} = 85 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \,^{\circ}C$.
- (3) $T_{amb} = -40 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -40 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

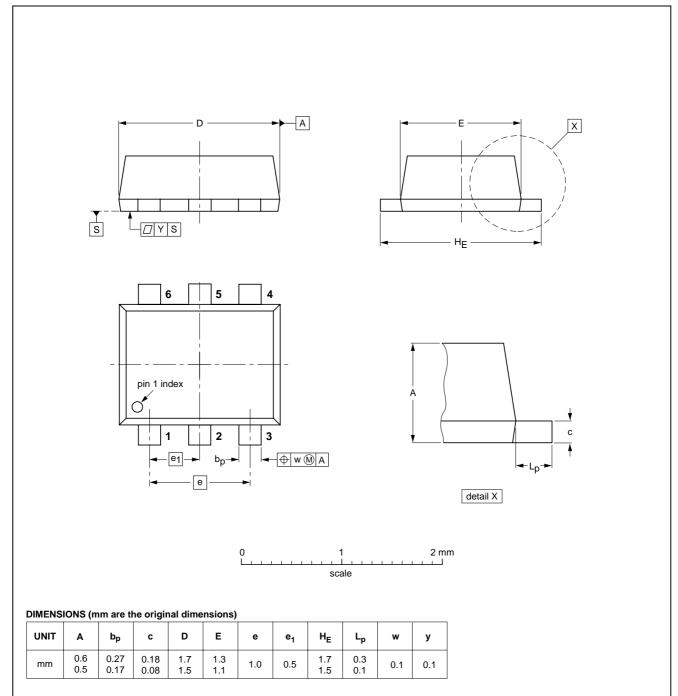
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



OUTLINE		REFERENCES			EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT666						-01-01-04 01-08-27	
	•			•	•	•	

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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